

# NCE N-Channel Enhancement Mode Power MOSFET

## Description

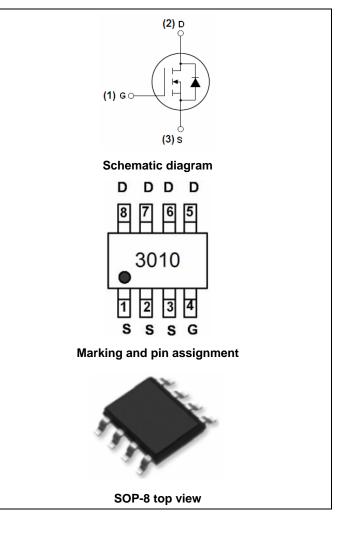
The NCE3010S uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

- V<sub>DS</sub> =30V,I<sub>D</sub> =10A
  R<sub>DS(ON)</sub> < 12mΩ @ V<sub>GS</sub>=10V
  R<sub>DS(ON)</sub> <16mΩ @ V<sub>GS</sub>=4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

#### Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



# Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3010	NCE3010S	SOP-8	Ø330mm	12mm	2500 units

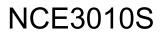
### Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	10	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	l <sub>D</sub> (100℃)	6	A
Pulsed Drain Current	I <sub>DM</sub>	50	A
Maximum Power Dissipation	PD	2.5	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C

### **Thermal Characteristic**

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-	Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	50	°C/W	ĺ





# Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	Р	$V_{GS}$ =10V, $I_{D}$ =10A	-	8	12	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, I <sub>D</sub> =5A	-	11	16	
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =10A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>Iss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	1550	-	PF
Output Capacitance	C <sub>oss</sub>		-	300	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	180	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	30	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =25V,I <sub>D</sub> =1A	-	20	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =6 $\Omega$	-	100	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	80	-	nS
Total Gate Charge	Qg	(-15)(1-100)	-	13	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =10A, V <sub>GS</sub> =5V	-	5.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	vc=sov	-	3.5	_	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	10	А

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

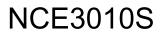
**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



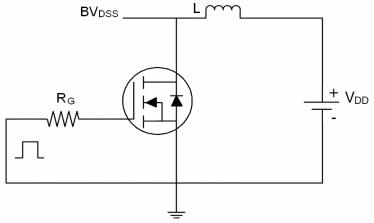
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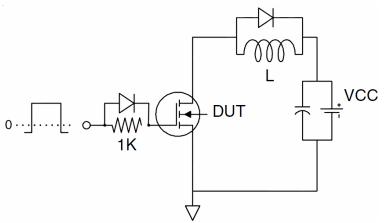


# **Test Circuit**

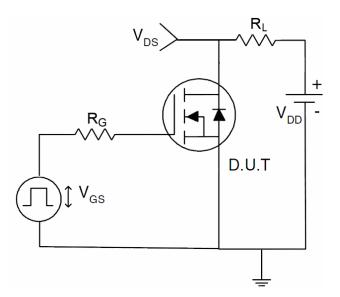
1) E<sub>AS</sub> Test Circuits



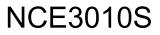
# 2) Gate Charge Test Circuit:



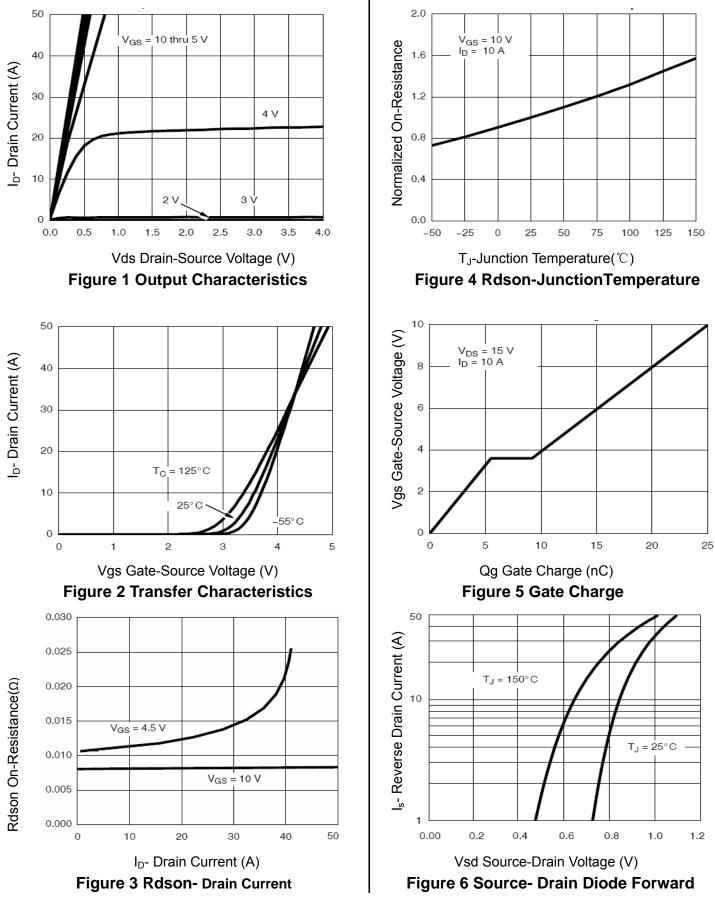
## 3) Switch Time Test Circuit:







# **Typical Electrical and Thermal Characteristics (Curves)**





100

10

1

0.1

0.01

0.1

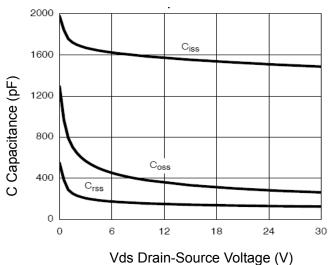
\*r<sub>DS(on)</sub> Limited

Ip- Drain Current (A)

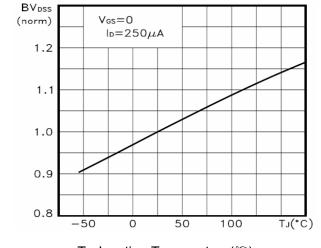
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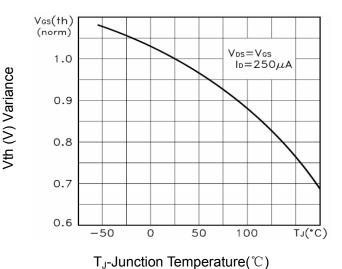
NCE3010S







TJ-Junction Temperature(℃) Figure 9 BV<sub>DSS</sub> vs Junction Temperature



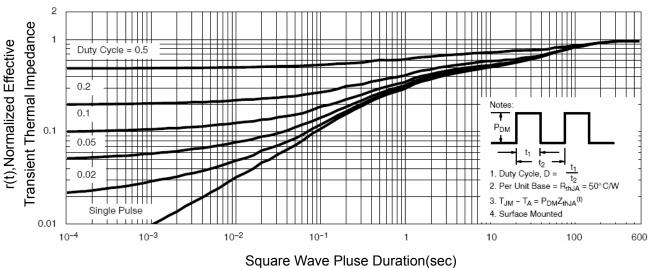
Vds Drain-Source Voltage (V) Figure 8 Safe Operation Area

10

T<sub>A</sub> = 25°C Single Pulse

1

Figure 10  $V_{GS(th)}$  vs Junction Temperature



Normalized BVdss

1 ms

10 ms

100 ms

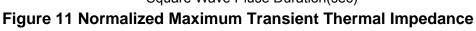
<del>111111</del> 1s

dc, 100 s

100

10 s

100 µs, 10 µs

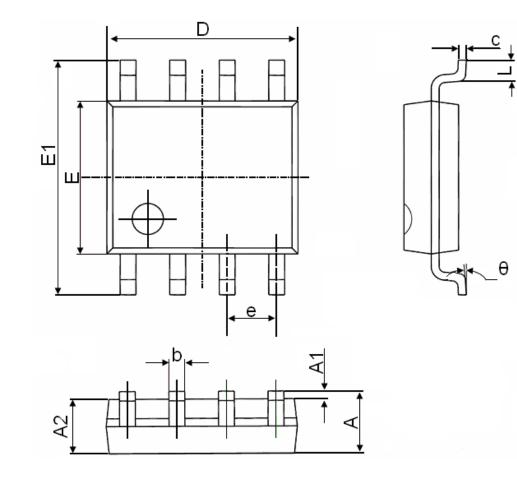




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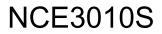
# SOP-8 Package Information



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	







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